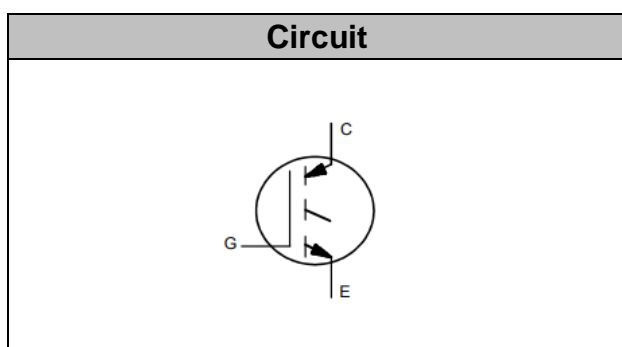


## IGBT Discrete

$V_{CE}$	1200	V
$I_C$	80	A
$V_{CE(SAT)} I_C=80A$	1.75	V



## Applications

- PTC

## Features

- High breakdown voltage to 1200V for improved reliability
- Maximum junction temperature 150°C
- Positive temperature coefficient
- Qualified to AEC-Q101

## Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter Breakdown Voltage	$V_{CE}$	1200	V
DC Collector Current, limited by $T_{jmax}$ $T_C=25^\circ C$ $T_C=100^\circ C$	$I_C$	145* 80	A
Continuous Gate-Emitter Voltage	$V_{GE}$	$\pm 20$	V
Transient Gate-Emitter Voltage ( $t_p \leq 10\mu s, D < 0.010$ )	$V_{GE}$	$\pm 30$	V
Turn off Safe Operating Area $V_{CE} \leq 1200V$ , $T_j \leq 150^\circ C$		240	A
Pulsed Collector Current, $V_{GE}=15V$ , $t_p$ limited by $T_{jmax}$	$I_{CM}$	240	A
Power Dissipation , $T_j=150^\circ C$ , $T_C=25^\circ C$	$P_{tot}$	521	W

\*Bond wire current limit is 80A



Operating Junction Temperature	$T_j$	-40...+150	°C
Storage Temperature	$T_s$	-55...+150	°C
Soldering Temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	°C

**Electrical Characteristics of the IGBT** ( $T_j = 25^\circ\text{C}$  unless otherwise specified):

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Collector-Emitter Breakdown Voltage	$BV_{CES}$	$V_{GE}=0V, I_C=1mA$	1200		-	V
Gate Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=2.6mA$	5.35	6.0	6.7	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=80A$ $T_j=25^\circ\text{C}$ , $T_j=125^\circ\text{C}$ $T_j=150^\circ\text{C}$	1.45	1.75 2.15 2.25	2.30	V
Zero Gate Voltage Collector Current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V$ $T_j=25^\circ\text{C}$ , $T_j=150^\circ\text{C}$			0.25 1.00	mA
Gate-Emitter Leakage Current	$I_{GES}$	$V_{CE}=0V, V_{GE}=\pm 20V$			$\pm 100$	nA

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Dynamic</b>						
Input Capacitance	$C_{ies}$	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz$	-	7.95	-	nF
Reverse Transfer Capacitance	$C_{res}$		-	0.19	-	
Gate Charge	$Q_G$	$V_{CC}=960V, I_C=80A,$ $V_{GE}=15V$	-	0.65	-	uC

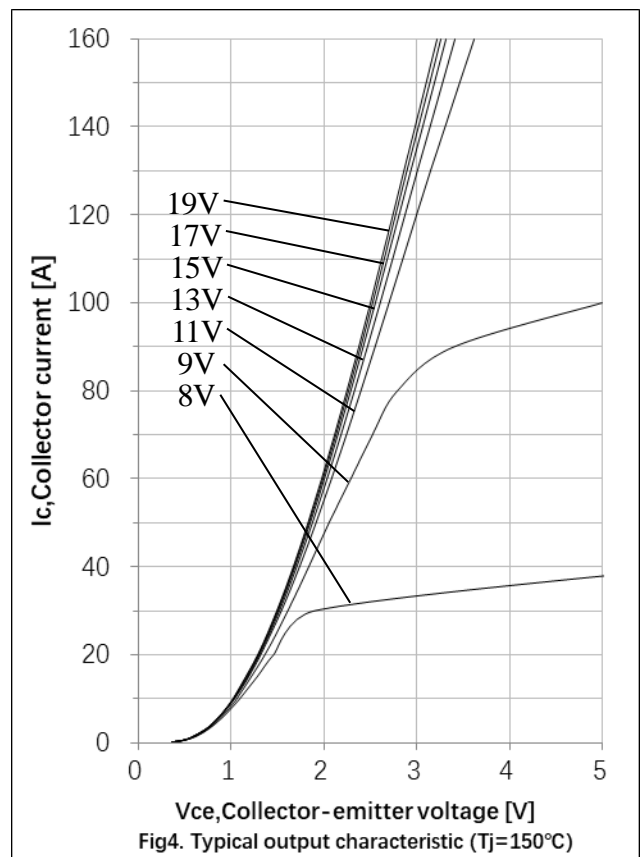
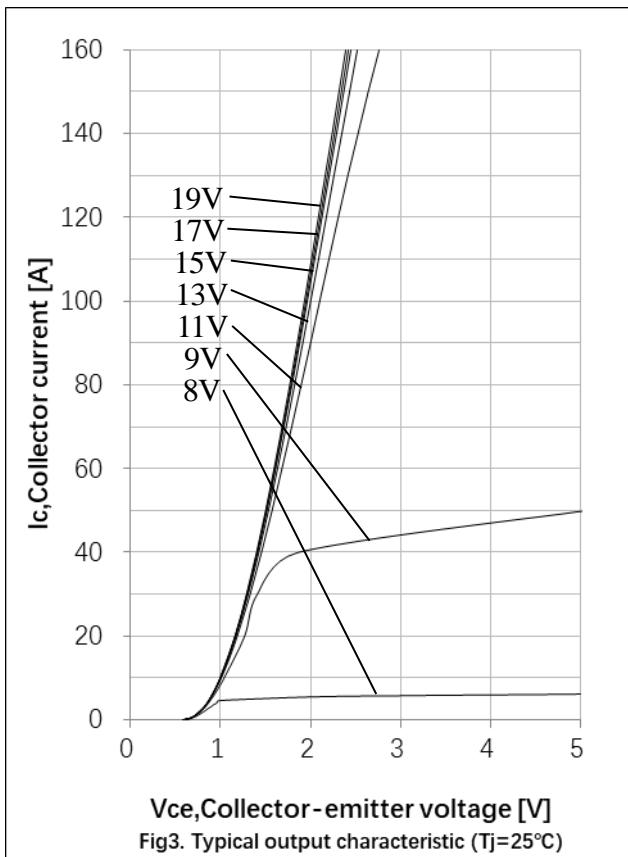
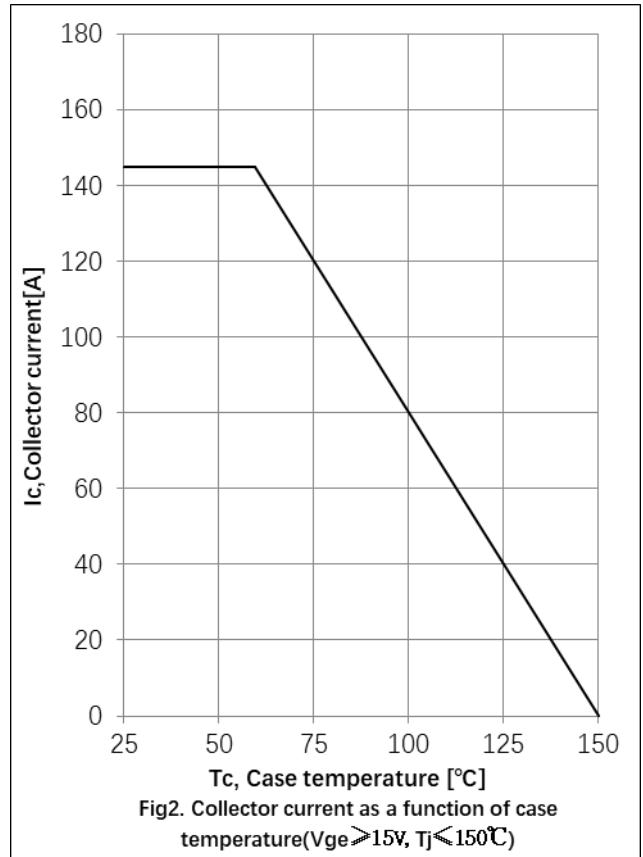
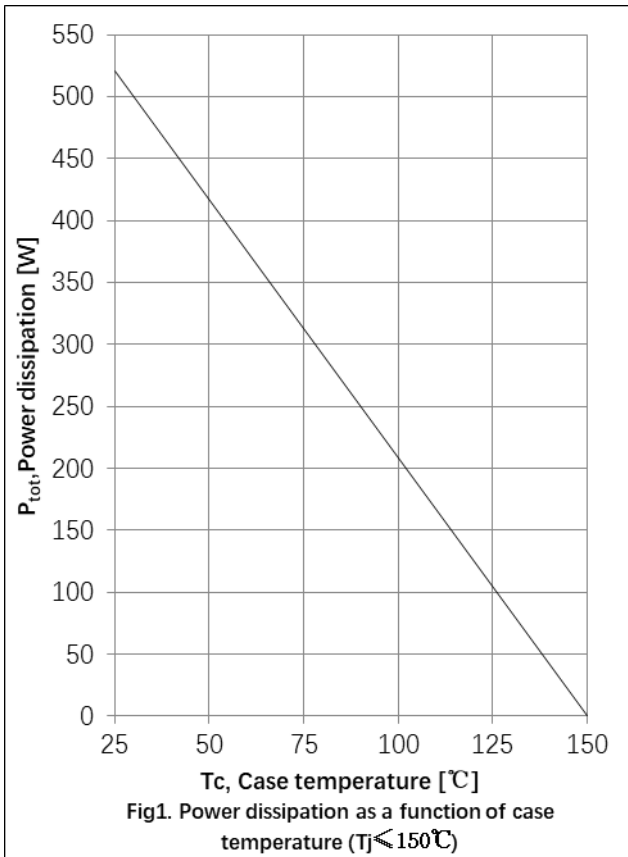


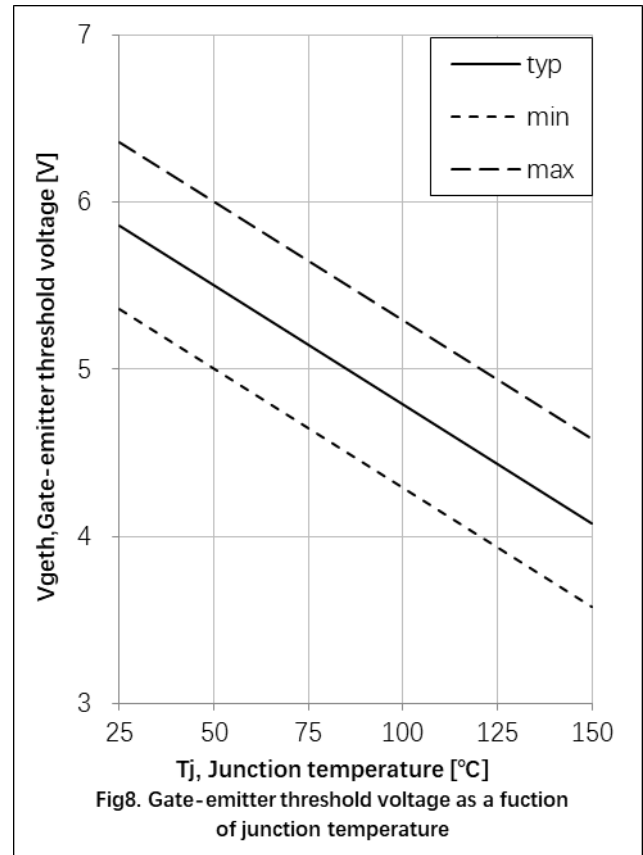
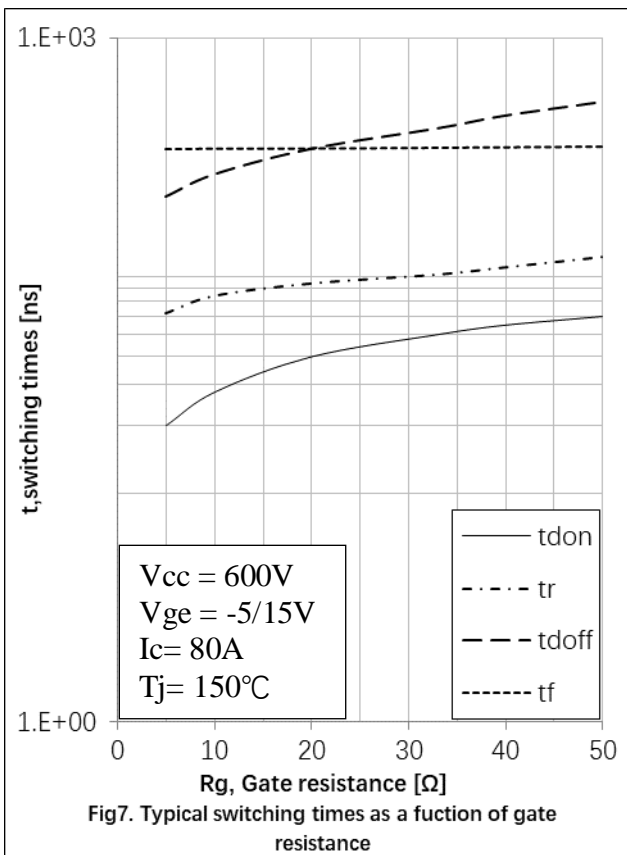
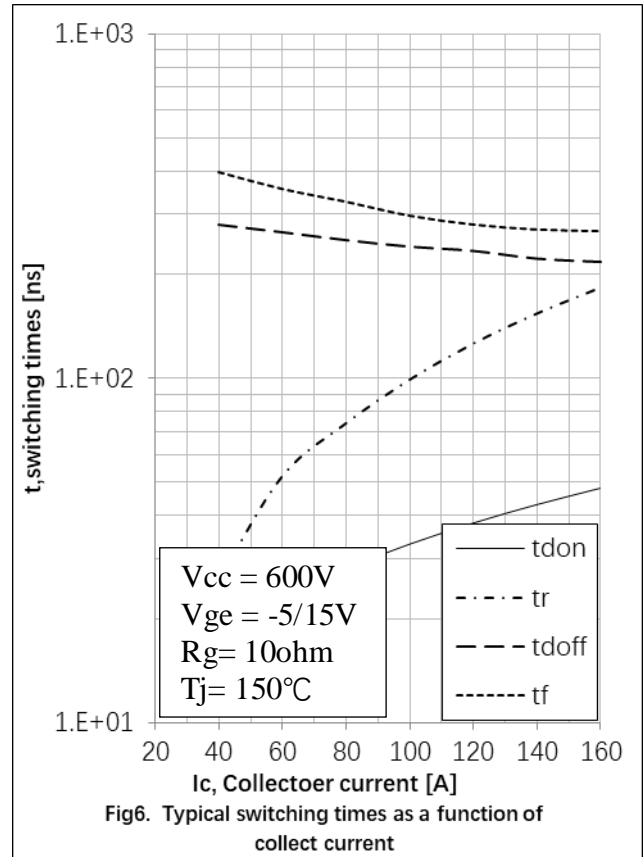
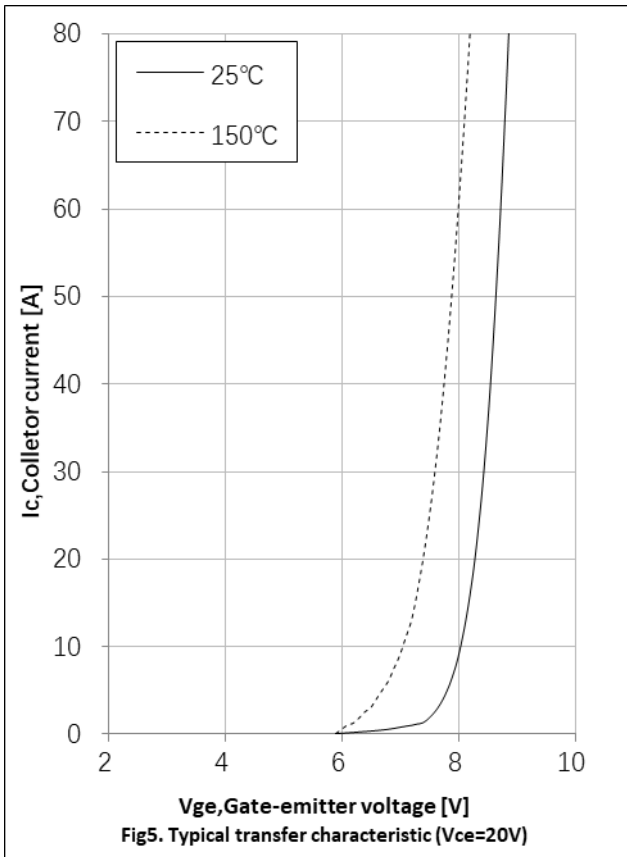
## Switching Characteristic, Inductive Load

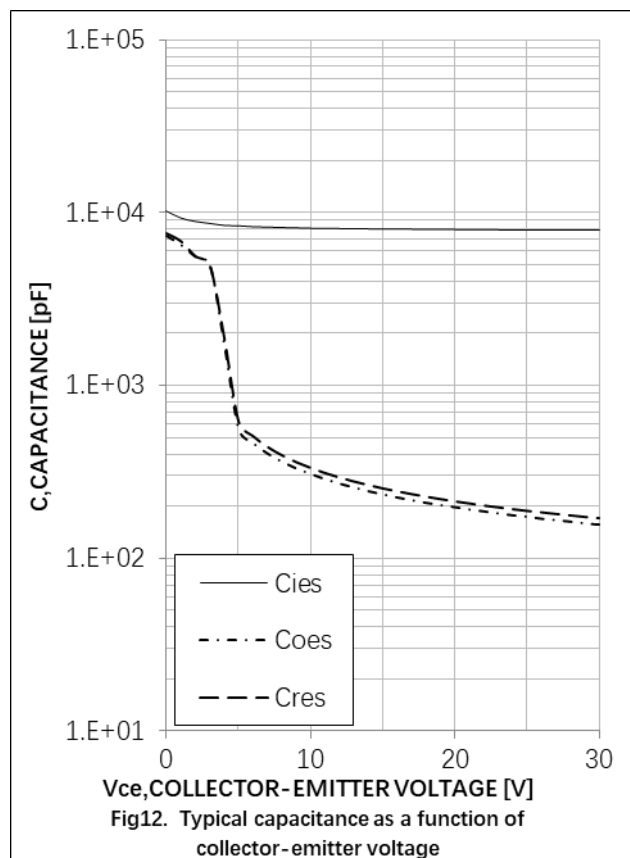
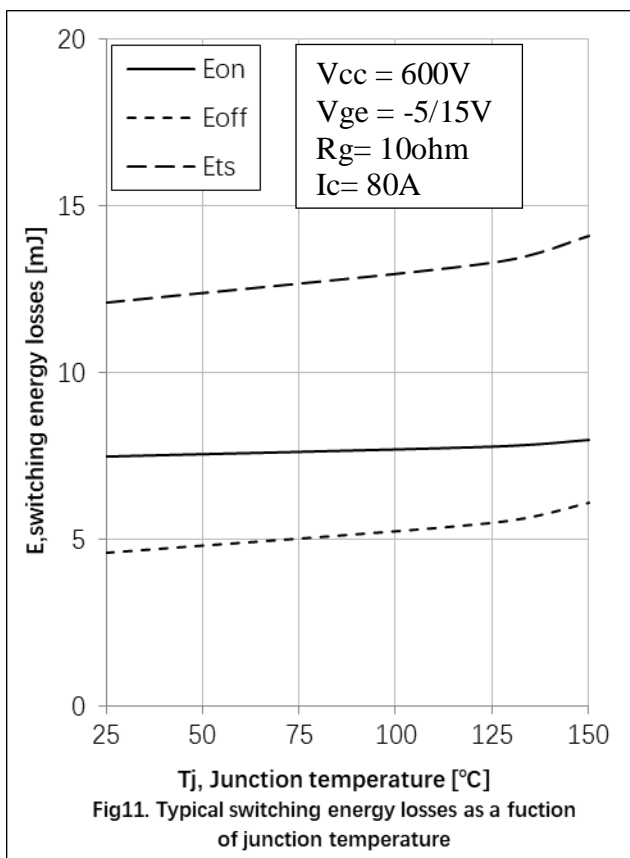
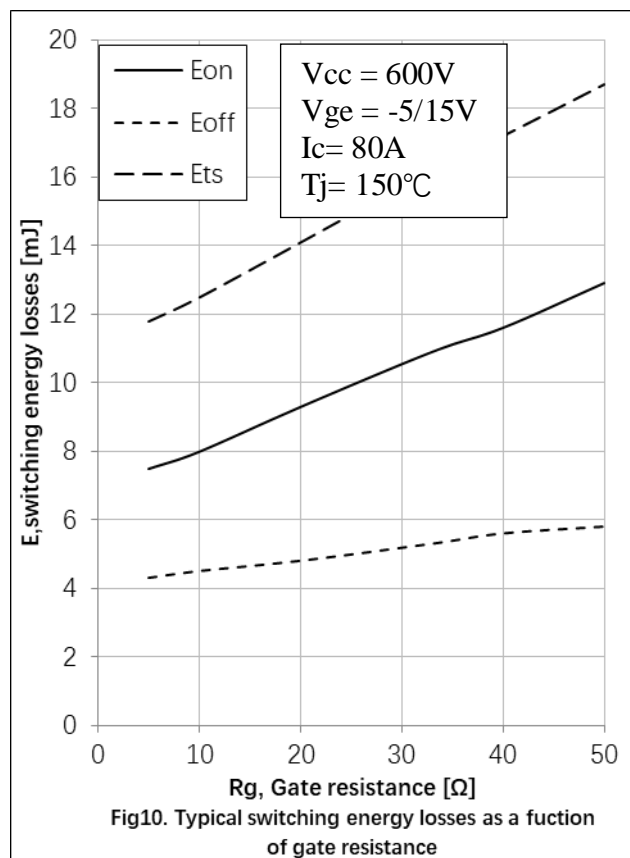
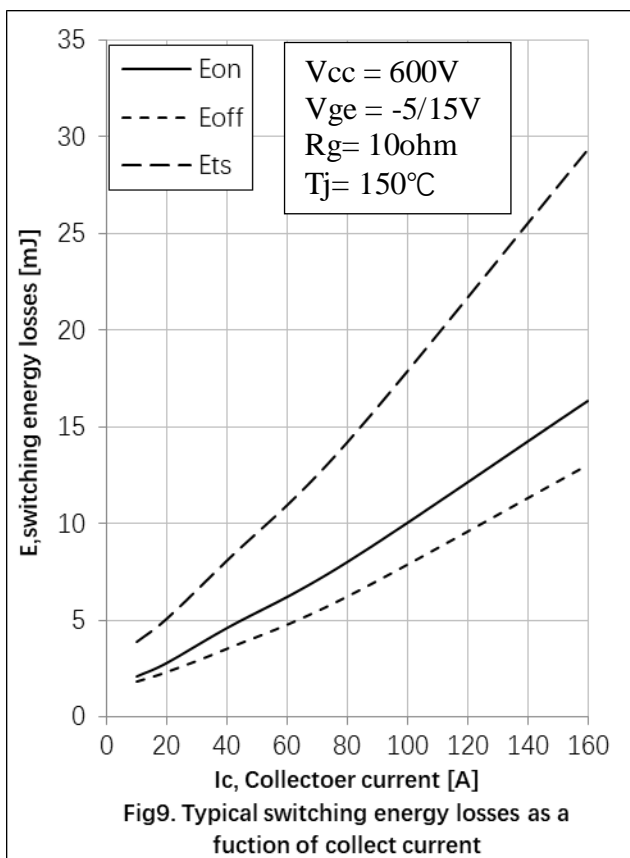
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Dynamic , at T<sub>j</sub>= 25°C</b>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>CC</sub> = 600V, I <sub>C</sub> =80A, V <sub>GE</sub> = -5V~15V, R <sub>g</sub> =10Ω	-	33	-	ns
Rise Time	t <sub>r</sub>		-	85	-	ns
Turn-on Energy	E <sub>on</sub>		-	7.5	-	mJ
Turn-off Delay Time	t <sub>d(off)</sub>		-	231	-	ns
Fall Time	t <sub>f</sub>		-	174	-	ns
Turn-off Energy	E <sub>off</sub>		-	4.6	-	mJ
<b>Dynamic , at T<sub>j</sub>= 125°C</b>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>CC</sub> = 600V, I <sub>C</sub> =80A, V <sub>GE</sub> = -5V~15V, R <sub>g</sub> =10Ω	-	30	-	ns
Rise Time	t <sub>r</sub>		-	79	-	ns
Turn-on Energy	E <sub>on</sub>		-	7.8	-	mJ
Turn-off Delay Time	t <sub>d(off)</sub>		-	243	-	ns
Fall Time	t <sub>f</sub>		-	263	-	ns
Turn-off Energy	E <sub>off</sub>		-	5.5	-	mJ
<b>Dynamic , at T<sub>j</sub>= 150°C</b>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>CC</sub> = 600V, I <sub>C</sub> =80A, V <sub>GE</sub> = -5V~15V, R <sub>g</sub> =10Ω	-	28	-	ns
Rise Time	t <sub>r</sub>		-	74	-	ns
Turn-on Energy	E <sub>on</sub>		-	8.0	-	mJ
Turn-off Delay Time	t <sub>d(off)</sub>		-	252	-	ns
Fall Time	t <sub>f</sub>		-	325	-	ns
Turn-off Energy	E <sub>off</sub>		-	6.2	-	mJ

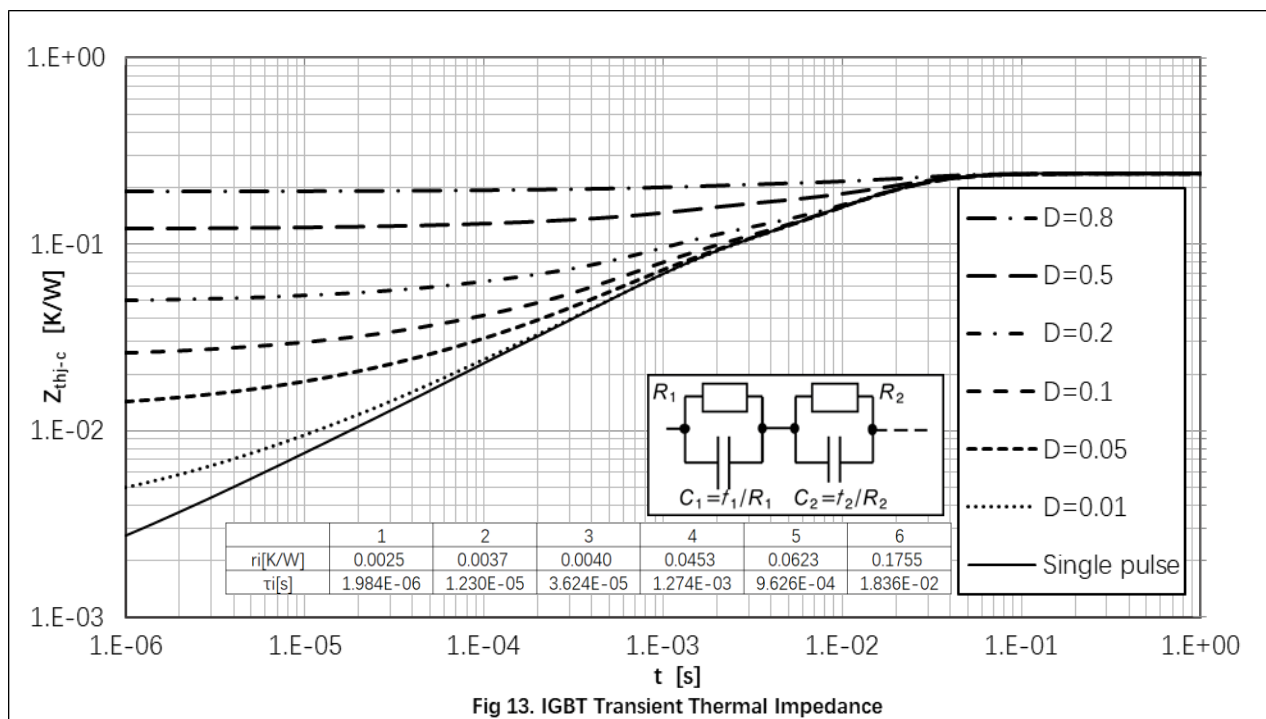
## Thermal Resistance

Parameter	Symbol	Max. Value	Unit
IGBT Thermal Resistance, Junction - Case	R <sub>th(j-c)</sub>	0.24	K/W
Thermal Resistance, Junction - Ambient	R <sub>th(j-a)</sub>	40	K/W

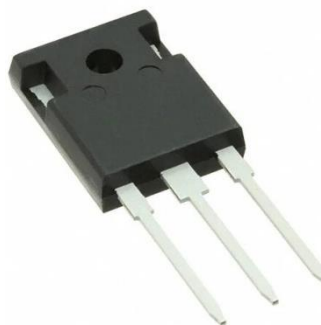
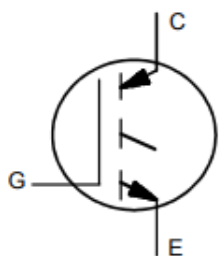




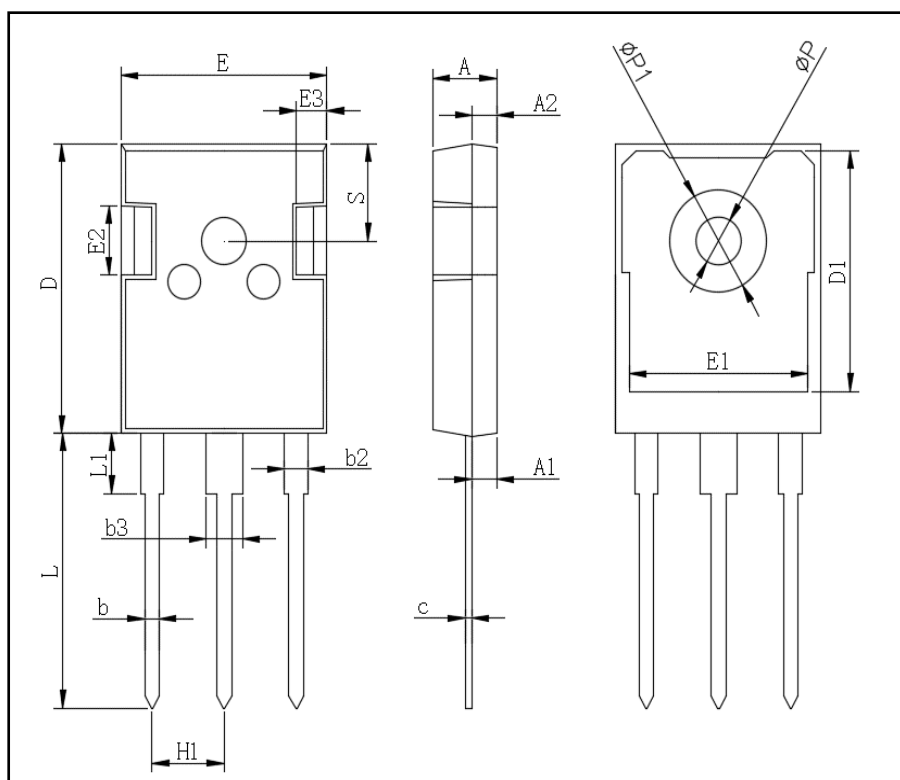




● **Circuit Diagram**



● **Package Outline Information**



TO-247AB		
Dim	Min	Max
A	4.80	5.20
A1	2.21	2.61
A2	1.85	2.15
b	1.0	1.4
b2	1.91	2.21
C	0.5	0.7
D	20.70	21.30
D1	16.25	16.85
E	15.50	16.10
E1	13.0	13.6
E2	4.80	5.20
E3	2.30	2.70
L	19.62	20.22
L1	-	4.30
Φ P	3.40	3.80
Φ P1	-	7.30
S	6.15TYP	
H1	5.44TYP	
b3	2.80	3.20





ISSUE	REVISION	DATE
1.0	Add Datasheet	2-Nov-22
1.1	Updated With $V_{GE(th)}$ Conditions Updated With $V_{GE(th)}$ Parameter Scope Update $V_{CE(SAT)}$ Parameter Scope	27-Jul-23